

PTO/SB/08a Substitute for Form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				Application Number	10/530,848
				Filing Date	April 8, 2005
				First Named Inventor	ARMIN ABERLE
				Art Unit	Not Yet Assigned
				Examiner Name	Not Yet Assigned
Sheet	1	of	2	Attorney Docket	85267

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup>			
/J.S./		US-5,275,851 A	01/04/1994	Fonash et al.	
/J.S./		US-5,344,796 A	09/06/1994	Shin et al.	
/J.S./		US-6,097,037 A	08/01/2000	Joo et al.	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup>				
/J.S./		EP 1 271 620 A1	01/02/2003	Hyoung June Kim		
/J.S./		JP 2002261305	09/13/2002	Toyota Central Res. & Dev. Lab Inc.		

Examiner Signature	/Julia Slutsker/	Date Considered	05/16/2008
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PTO/SB/08b Substitute for Form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)		Application Number	10/530,848		
		Filing Date	April 8, 2005		
		First Named Inventor	ARMIN ABERLE		
		Art Unit	Not Yet Assigned		
		Examiner Name	Not Yet Assigned		
Sheet	2	of	2	Attorney Docket	85267

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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